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520.37546X00

5/20/3
Sunder

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: K. TORII, et al.
Application No.: 09/391,250
Filed: September 7, 1999
For: MEMORY STRUCTURE WITH A FERROELECTRIC
CAPACITOR AND A FABRICATION METHOD
THEREOF (As amended)
Group: 2811
Examiner: C. Nguyen

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

May 12, 2003

Sir:

In response to the Office Action dated January 10, 2003, the period of response for

05/21/2003 SSURLEY which extends to 1999-2003
Sale Ref: 00000004 DAW: 012135 09391250
01 FC:1202 72.00 CH
02 FC:1201 168.00 CH
the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 7 as follows:

1. (Twice Amended) A semiconductor device comprising:
- an insulating film formed on a substrate provided with a transistor and having an opening portion;
- a conductive film formed in the opening portion; and